

isc N-Channel MOSFET Transistor

IRF8010, IIRF8010

FEATURES

- Static drain-source on-resistance: R_Ds(on) ≤15mΩ
- Enhancement mode
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

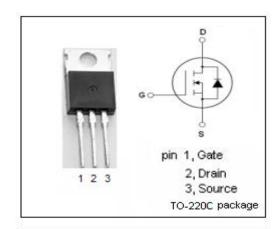
• reliable device for use in a wide variety of applications

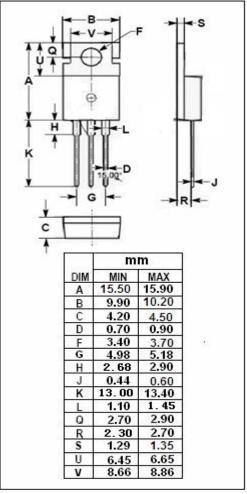
• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

ABOOLOTE INACIMONI (ATINOO(1a 200)							
SYMBOL	PARAMETER	VALUE	UNIT				
V _{DSS}	Drain-Source Voltage	100	V				
V _{GS}	Gate-Source Voltage	±20	V				
I _D	Drain Current-Continuous	80	А				
I _{DM}	Drain Current-Single Pulsed	320	А				
P _D	Total Dissipation @T _C =25°C	260	W				
Tj	Max. Operating Junction Temperature	175	$^{\circ}$ C				
T _{stg}	Storage Temperature	-55~175	$^{\circ}$ C				

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.57	°C/W
Rth(ch-a)	Rth(ch-a) Channel-to-ambient thermal resistance		°C/W







isc N-Channel MOSFET Transistor

IRF8010, IIRF8010

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID =250 μ A	100			V
$V_{\text{GS(th)}}$	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID =250 μ A	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =45A			15	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V			±0.2	μ А
I _{DSS}	Drain-Source Leakage Current	V _{DS} =100V; V _{GS} = 0V			20	μА
V _{SD}	Diode forward voltage	Is=80A, V _{GS} = 0V			1.3	V

NOTICE:

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications. ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.